

30V N-Channel MOSFET

Product Summary

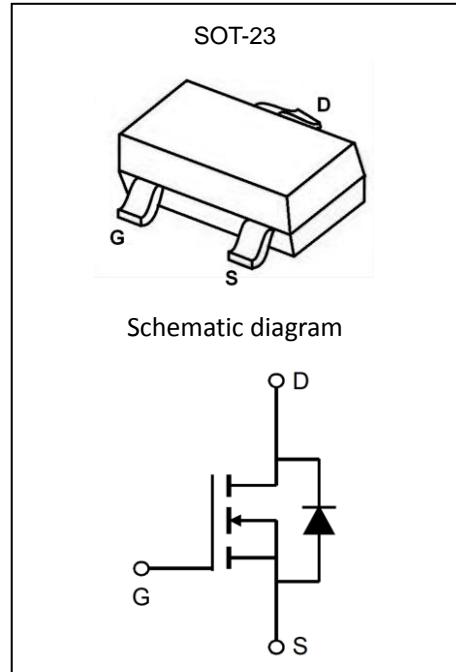
$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
30V	30mΩ@10V	5.8A
	42mΩ@4.5V	

Feature

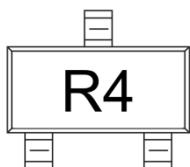
- TrenchFET Power MOSFET
- Excellent $R_{DS(on)}$ and Low Gate Charge
- AEC-Q101 qualified (Automotive grade with suffix "Q".)
- Expsemi electronics

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch
- AEC-Q101 qualified



MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	5.8	A
Pulsed Drain Current	I_{DM}	30	A
Power Dissipation*	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

* Repetitive rating : Pulse width limited by maximum junction temperature.

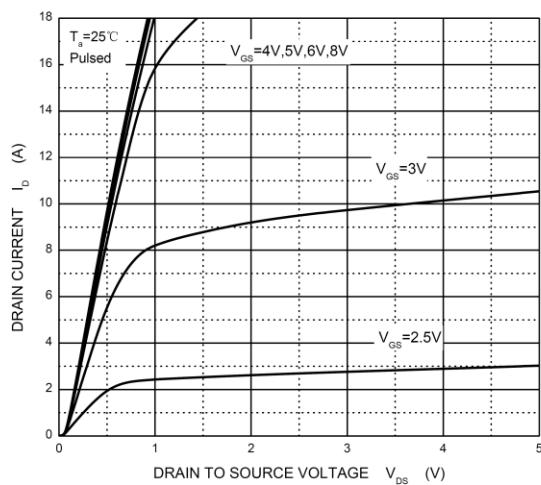
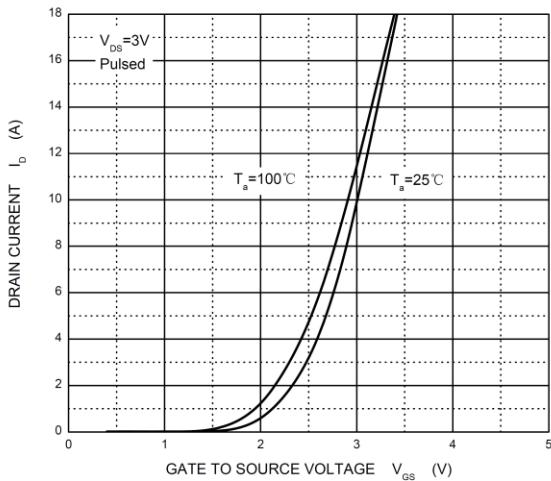
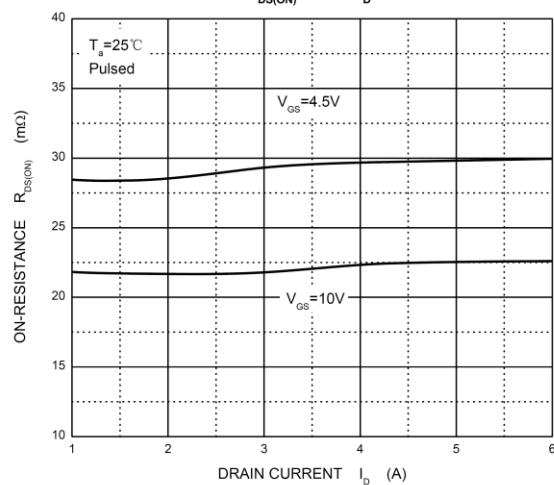
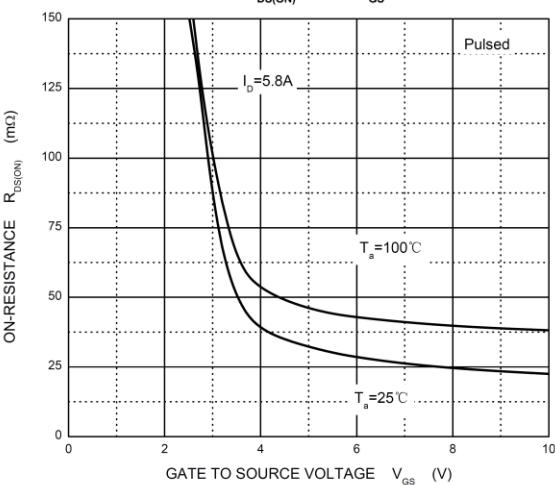
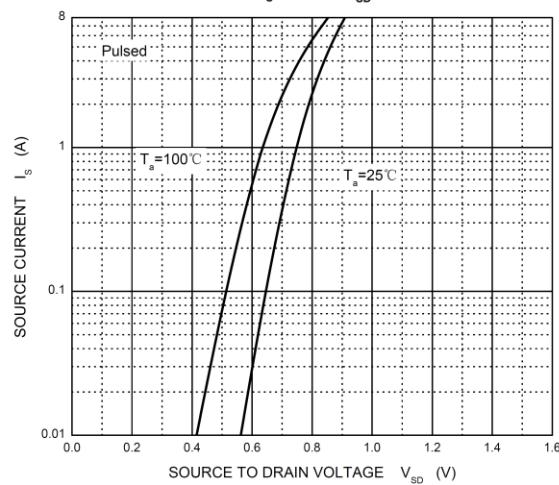
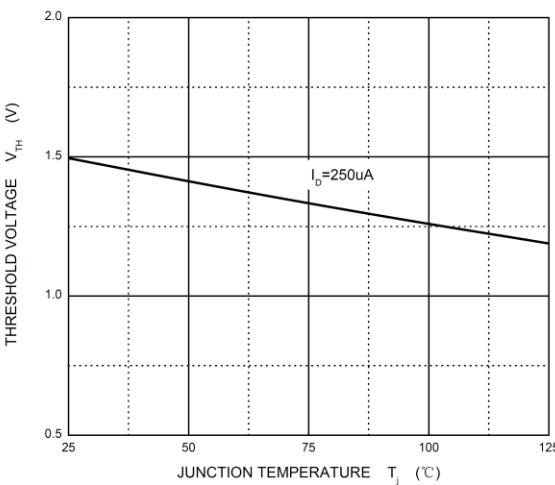
MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	30			V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 30\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}, V_{\text{DS}} = 0\text{V}$			± 100	nA
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	1	1.5	3	V
Drain-source on-resistance ⁽¹⁾	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 5.8\text{A}$		21	30	$\text{m}\Omega$
		$V_{\text{GS}} = 4.5\text{V}, I_D = 4.8\text{A}$		28	42	
Forward transconductance ⁽¹⁾	g_{FS}	$V_{\text{DS}} = 5\text{V}, I_D = 3.8\text{A}$	5			S
Body Diode Voltage	V_{SD}	$I_S = 1\text{A}, V_{\text{GS}} = 0\text{V}$			1	V
DYNAMIC CHARACTERISTICS⁽²⁾						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 15\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$			810	pF
Output Capacitance	C_{oss}			115		
Reverse Transfer Capacitance	C_{rss}			83		
Gate resistance	R_g	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$			1.5	Ω
SWITCHING CHARACTERISTICS⁽²⁾						
Turn-on delay time	$t_{d(\text{on})}$	$V_{\text{GS}} = 10\text{V}, V_{\text{DS}} = 15\text{V}, R_L = 2.6\Omega, R_{\text{GEN}} = 6\Omega$			6.4	ns
Turn-on rise time	t_r			3.1		
Turn-off delay time	$t_{d(\text{off})}$			15.0		
Turn-off fall time	t_f			2.6		

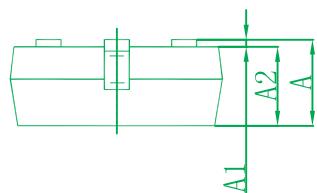
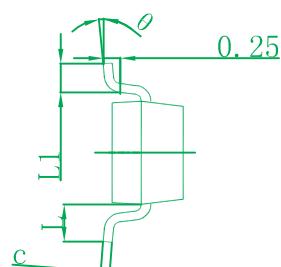
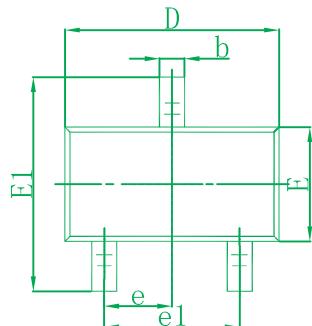
Notes:

1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 0.5\%$.
2. These parameters have no way to verify.

Typical Electrical and Thermal Characteristics

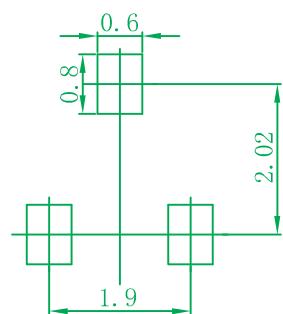
Output Characteristics

Transfer Characteristics

 $R_{DS(ON)}$ — I_D

 $R_{DS(ON)}$ — V_{GS}

 I_S — V_{SD}

Threshold Voltage


SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.150	0.035	0.045
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.050	0.110	0.120
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.360 REF		0.014 REF	
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

Ordering information

Device	Package	Shipping
EP3404	SOT-23	3000/Tape&Reel(7inches)